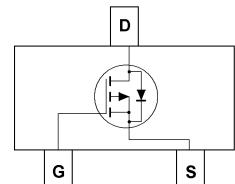


## P-Channel Enhancement Mode MOSFET

### Feature

- 20V/-3A R<sub>DS(ON)</sub> = 120mΩ(MAX) @V<sub>GS</sub> = -4.5V.  
R<sub>DS(ON)</sub> = 150mΩ(MAX) @V<sub>GS</sub> = -2.5V.
- Super High dense cell design for extremely low R<sub>DS(ON)</sub>
- Reliable and Rugged
- SC-59 for Surface Mount Package



SC-59

### Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

### Absolute Maximum Ratings

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Drain Current-Continuous	I <sub>D</sub>	-3	A

### Electrical Characteristics

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	-20	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	V <sub>GS</sub> =10V, V <sub>DS</sub> =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V <sub>GS</sub> =-10V, V <sub>DS</sub> =0V	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> =250μA	-0.4	-	-1.0	V
Static Drain-source	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.0A	-	--	120	mΩ
On-Resistance		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A	-	--	150	mΩ
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1.25A			-1.2	V

## Typical Characteristics

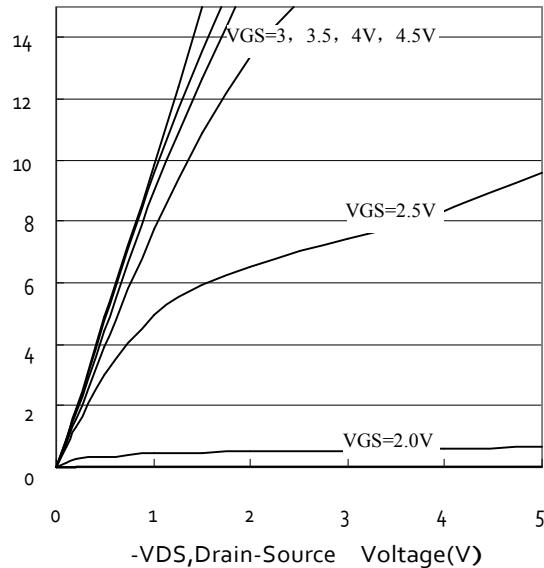


Figure 1. Output Characteristics

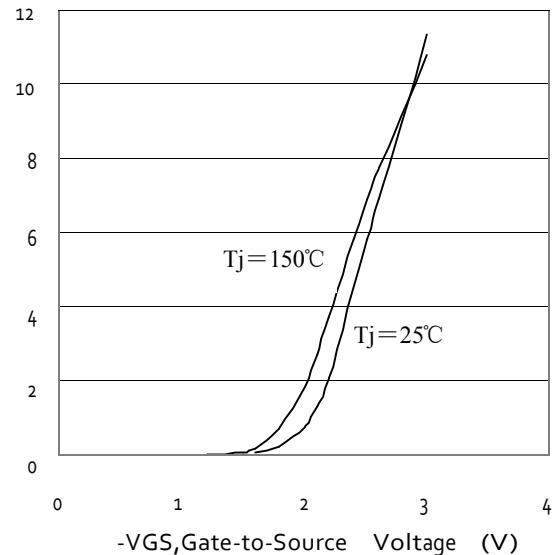


Figure 2. Transfer Characteristics

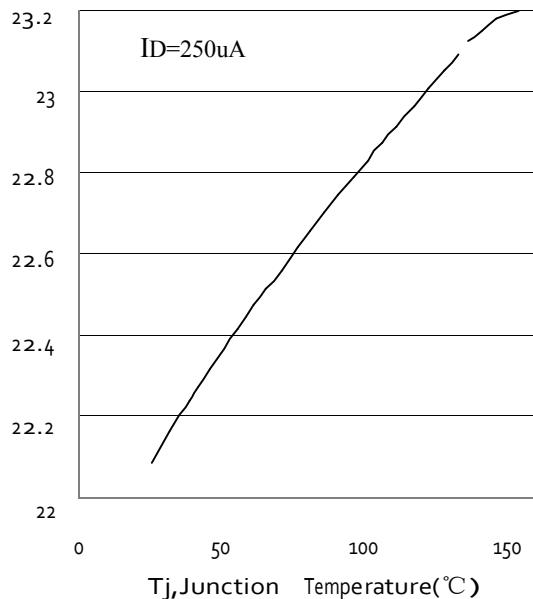


Figure 3. Breakdown Voltage Variation with Temperature

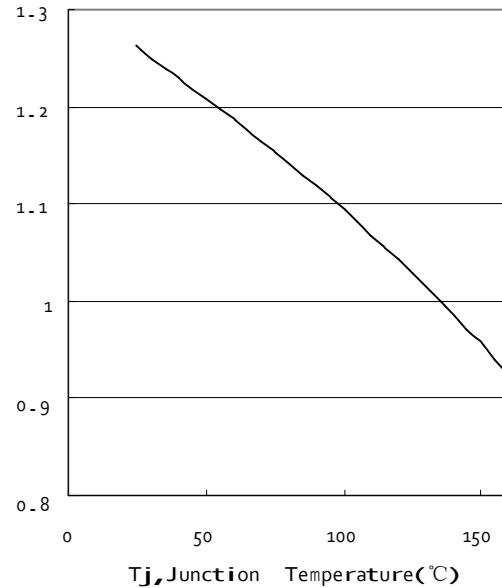


Figure 4. Gate Threshold Variation with Temperature

## Typical Characteristics

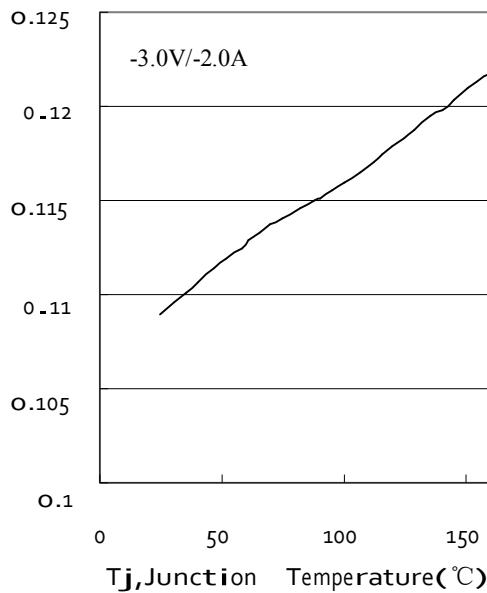


Figure 5. On-Resistance Variation with Temperature

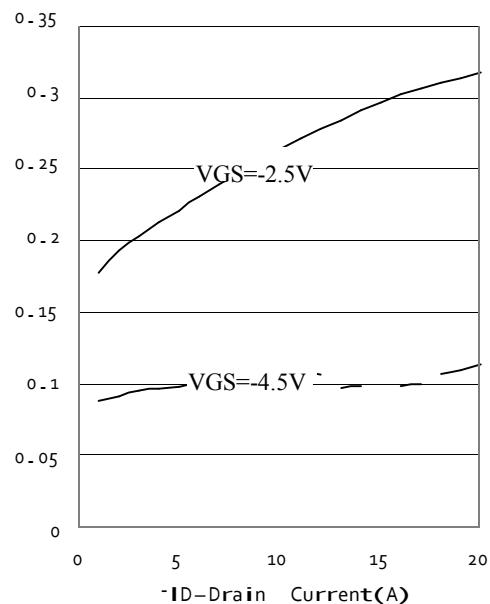


Figure 6. On-Resistance vs. Drain Current

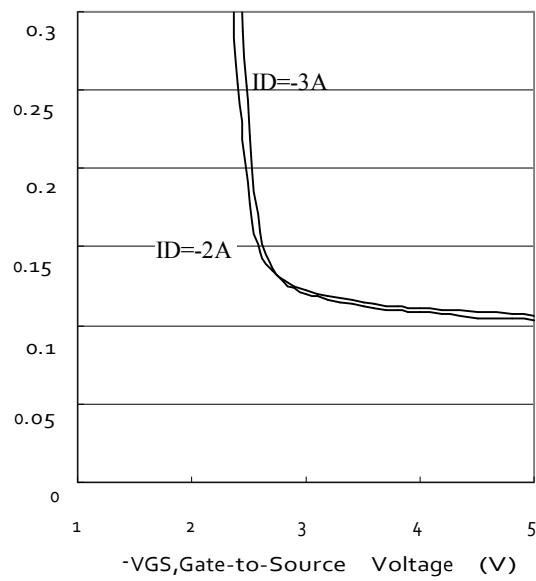


Figure 7 . On-Resistance vs. Gate-to-Source Voltage

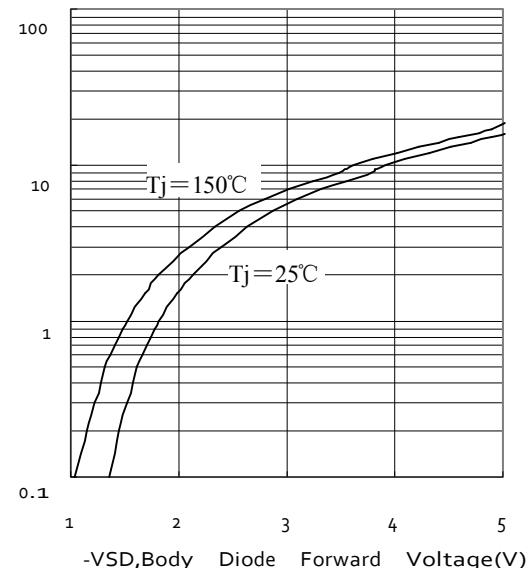
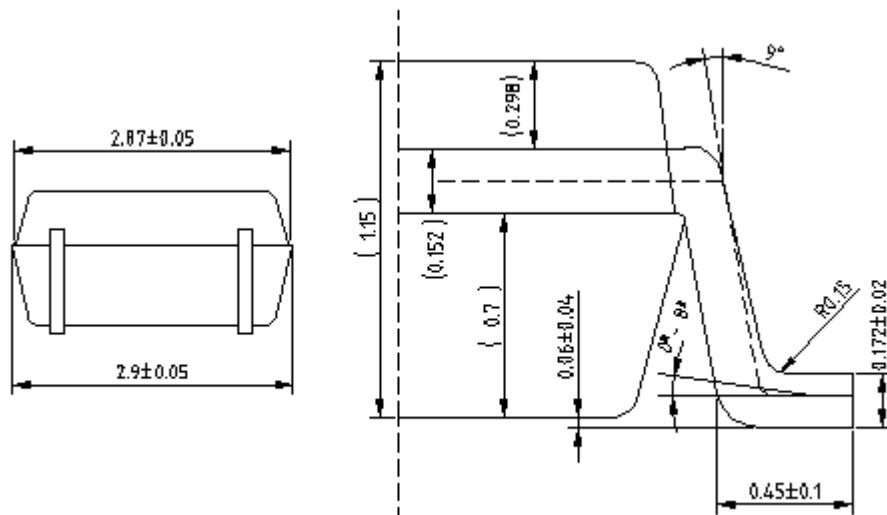
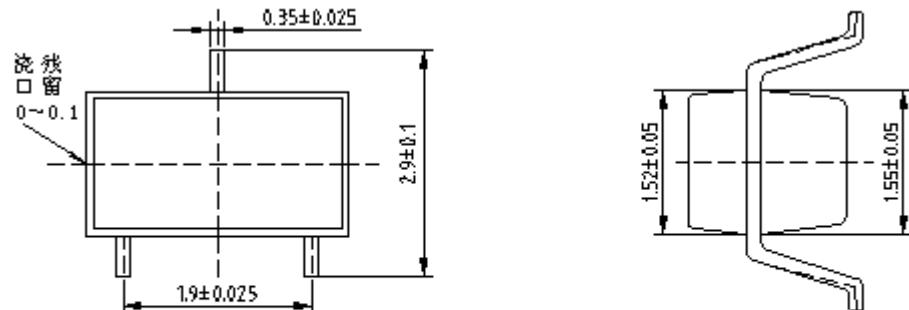


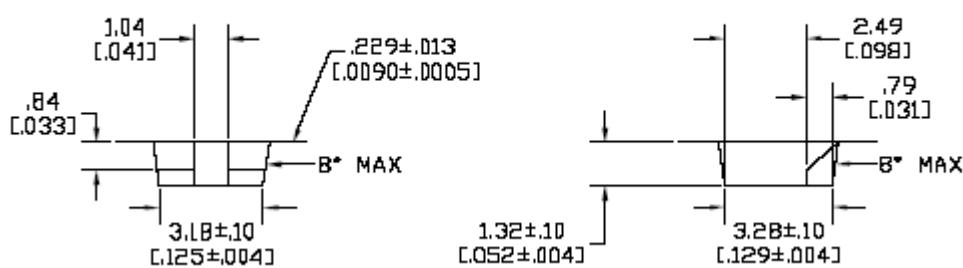
Figure 8 . Source-Drain Diode Forward Voltage

Package Outline Dimensions (UNIT: mm)

SC-59



SC-59 Carrier Tape



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